ABSTRACT OF THE DISCLOSURE

SEMICONDUCTOR DEVICE HAVING A DUAL STRESS LINER, METHOD OF MANUFACTURING THE SEMICONDUCTOR DEVICE AND LIGHT EXPOSURE APPARATUS FOR FORMING THE DUAL STRESS LINER

In a semiconductor device having a dual stress liner for improving electron mobility, the dual stress liner includes a first liner portion formed on a PMOSFET and a second liner portion formed on an NMOSFET. The first liner portion has a first compressive stress, and the second liner portion has a second compressive stress smaller than the first compressive stress. The dual stress liner may be formed by forming a stress liner on a semiconductor substrate on which the PMOSFET and the NMOSFET are formed and selectively exposing a portion of the stress liner on the NMOSFET.

Figure 6